# 1. General description

NPN/PNP general-purpose transistors in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- General-purpose transistor
- High current
- Reduces component count on Printed-Circuit Board (PCB)
- · Reduces pick and place costs
- AEC-Q101 qualified

# 3. Applications

- · General-purpose switching and amplification
- Complementary driver
- · Half-bridge and full-bridge driver

## 4. Quick reference data

#### Table 1. Quick reference data

| Symbol          | Parameter                 | Conditions   | Min | Тур | Max | Unit |  |  |
|-----------------|---------------------------|--|-----|-----|-----|------|--|--|
| TR1 (NPN)       | TR1 (NPN)                 |  |     |     |     |      |  |  |
| $V_{CEO}$       | collector-emitter voltage | open base  | -   | -   | 40  | V    |  |  |
| h <sub>FE</sub> | DC current gain           | $V_{CE}$ = 10 V; $I_{C}$ = 150 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C   | 100 | -   | 300 |      |  |  |
| TR2 (PNP)       | ·                         |  |     |     |     |      |  |  |
| $V_{CEO}$       | collector-emitter voltage | open base  | -   | -   | -60 | V    |  |  |
| h <sub>FE</sub> | DC current gain           | $V_{CE}$ = -10 V; $I_{C}$ = -150 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C | 100 | -   | 300 |      |  |  |
| Per transist    | tor; for the PNP transist | or with negative polarity  | '   | '   |     | ,    |  |  |
| I <sub>C</sub>  | collector current         |  | -   | -   | 600 | mA   |  |  |



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# 5. Pinning information

## **Table 2. Pinning information**

| Pin | Symbol | Description   | Simplified outline        | Graphic symbol         |
|-----|--------|---------------|---------------------------|------------------------|
| 1   | B1     | base TR1      | <u> </u>                  | C1 E1 C2               |
| 2   | E2     | emitter TR2   |                           |                        |
| 3   | B2     | base TR2      | <u>0</u> <u>1 1 2 1</u> 3 | TR1 TR2                |
| 4   | C2     | collector TR2 | TSOP6 (SOT457)            |                        |
| 5   | E1     | emitter TR1   |                           | D4 50 00               |
| 6   | C1     | collector TR1 |                           | B1 E2 B2<br>aaa-022995 |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package |  |         |  |  |
|-------------|---------|--|---------|--|--|
|             | Name    | Description                                      | Version |  |  |
| NMB2227A    | TSOP6   | plastic surface-mounted package (TSOP6); 6 leads | SOT457  |  |  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| NMB2227A    | 3B           |

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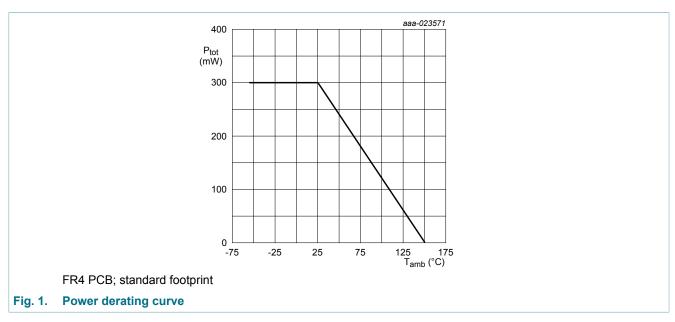
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                      | Conditions                          |     | Min | Max | Unit |
|------------------|--------------------------------|-------------------------------------|-----|-----|-----|------|
| TR1 (NPN)        |                                |                                     |     |     |     |      |
| V <sub>CBO</sub> | collector-base voltage         | open emitter                        |     | -   | 75  | V    |
| V <sub>CEO</sub> | collector-emitter voltage      | open base                           |     | -   | 40  | V    |
| TR2 (PNP)        |                                |                                     |     |     |     |      |
| V <sub>CBO</sub> | collector-base voltage         | open emitter                        |     | -   | -60 | V    |
| V <sub>CEO</sub> | collector-emitter voltage      | open base                           |     | -   | -60 | V    |
| Per transisto    | or; for the PNP transistor wit | h negative polarity                 |     |     |     |      |
| V <sub>EBO</sub> | emitter-base voltage           | open collector                      |     | -   | 6   | V    |
| I <sub>C</sub>   | collector current              |                                     |     | -   | 600 | mA   |
| I <sub>CM</sub>  | peak collector current         | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 800 | mA   |
| I <sub>BM</sub>  | peak base current              |                                     |     | -   | 200 | mA   |
| P <sub>tot</sub> | total power dissipation        | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 200 | mW   |
| Per device       |                                |                                     | ·   | ·   |     |      |
| P <sub>tot</sub> | total power dissipation        | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 300 | mW   |
| Tj               | junction temperature           |                                     |     | -   | 150 | °C   |
| T <sub>amb</sub> | ambient temperature            |                                     |     | -55 | 150 | °C   |
| T <sub>stg</sub> | storage temperature            |                                     |     | -65 | 150 | °C   |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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# 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

| Symbol        | Parameter                                   | Conditions  |     | Min | Тур | Max | Unit |
|---------------|---|-------------|-----|-----|-----|-----|------|
| Per transisto | or  |             |     |     |     |     |      |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] | -   | -   | 625 | K/W  |
| Per device    |   |             |     |     |     |     |      |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] | -   | -   | 417 | K/W  |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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# 10. Characteristics

#### **Table 7. Characteristics**

| Symbol                      | Parameter                            | Conditions  | Min | Тур | Max | Unit |
|-----------------------------|--------------------------------------|---|-----|-----|-----|------|
| TR1 (NPN)                   | ,                                    |   |     |     |     |      |
| I <sub>CBO</sub>            | collector-base cut-off               | V <sub>CB</sub> = 60 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C  | -   | -   | 10  | nA   |
|                             | current                              | V <sub>CB</sub> = 60 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 125 °C   | -   | -   | 10  | μA   |
| I <sub>EBO</sub>            | emitter-base cut-off current         | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$  | -   | -   | 10  | nA   |
| h <sub>FE</sub>             | DC current gain                      | V <sub>CE</sub> = 10 V; I <sub>C</sub> = 1 mA; T <sub>amb</sub> = 25 °C   | 50  | -   | -   |      |
|                             |                                      | V <sub>CE</sub> = 10 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C  | 75  | -   | -   |      |
|                             |                                      | $V_{CE}$ = 10 V; $I_{C}$ = 150 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C   | 100 | -   | 300 |      |
|                             |                                      | $V_{CE}$ = 10 V; $I_{C}$ = 500 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C                                  | 40  | -   | -   |      |
| V <sub>CEsat</sub>          | collector-emitter saturation voltage | $I_C$ = 150 mA; $I_B$ = 15 mA; pulsed; $t_p \le$ 300 µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C  | -   | -   | 300 | mV   |
|                             |                                      | $I_C$ = 500 mA; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C  | -   | -   | 1   | V    |
| V <sub>BEsat</sub> base-emi | base-emitter saturation voltage      | $I_C$ = 150 mA; $I_B$ = 15 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C   | 0.6 | -   | 1.2 | V    |
|                             |                                      | $I_C$ = 500 mA; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C  | -   | -   | 2   | V    |
| t <sub>d</sub>              | delay time                           | I <sub>C</sub> = 150 mA; I <sub>Bon</sub> = 15 mA;<br>I <sub>Boff</sub> = -15 mA; V <sub>CC</sub> = 10 V;<br>T <sub>amb</sub> = 25 °C | -   | -   | 15  | ns   |
| t <sub>r</sub>              | rise time                            |   | -   | -   | 20  | ns   |
| t <sub>on</sub>             | turn-on time                         |   | -   | -   | 35  | ns   |
| t <sub>s</sub>              | storage time                         |   | -   | -   | 200 | ns   |
| t <sub>f</sub>              | fall time                            |   | -   | -   | 60  | ns   |
| t <sub>off</sub>            | turn-off time                        |   | -   | -   | 250 | ns   |
| C <sub>C</sub>              | collector capacitance                | $V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C   | -   | -   | 8   | pF   |
| C <sub>E</sub>              | emitter capacitance                  | $V_{EB}$ = 500 mV; $I_{C}$ = 0 A; $i_{c}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C   | -   | -   | 25  | pF   |
| f <sub>T</sub>              | transition frequency                 | $V_{CE}$ = 20 V; $I_{C}$ = 20 mA; f = 100 MHz; $T_{amb}$ = 25 °C  | 300 | -   | -   | MHz  |
| TR2 (PNP)                   |                                      | '   |     | 1   | 1   |      |
| I <sub>CBO</sub>            | collector-base cut-off               | V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C   | -   | -   | -10 | nA   |
|                             | current                              | V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 125 °C  | -   | -   | -10 | μA   |
| I <sub>EBO</sub>            | emitter-base cut-off current         | V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C  | -   | -   | -50 | nA   |
| h <sub>FE</sub>             | DC current gain                      | V <sub>CE</sub> = -10 V; I <sub>C</sub> = -0.1 mA; T <sub>amb</sub> = 25 °C   | 75  | -   | -   |      |
|                             |                                      | V <sub>CE</sub> = -10 V; I <sub>C</sub> = -1 mA; T <sub>amb</sub> = 25 °C   | 100 | -   | -   |      |
|                             |                                      | V <sub>CE</sub> = -10 V; I <sub>C</sub> = -10 mA; T <sub>amb</sub> = 25 °C  | 100 | -   | -   |      |

## 40 V, 600 mA NPN/PNP general-purpose transistors

| Symbol  | Parameter   | Conditions  | I | Min | Тур  | Max  | Unit |
|---|---|---|---|-----|------|------|------|
|   |   | $V_{CE}$ = -10 V; $I_{C}$ = -150 mA; pulsed; $t_{p} \le$ 300 $\mu$ s; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C |   | 100 | -    | 300  |      |
|   |   | $V_{CE}$ = -10 V; $I_{C}$ = -500 mA; pulsed; $t_{p} \le$ 300 $\mu$ s; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C | ţ | 50  | -    | -    |      |
| V <sub>CEsat</sub> collector-emitter saturation voltage |   | $I_C$ = -150 mA; $I_B$ = -15 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C                       | - | -   | -    | -400 | mV   |
|   | $I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C | -   | - | -   | -1.6 | V    |      |
| DESGL   | base-emitter saturation voltage   | $I_C$ = -150 mA; $I_B$ = -15 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C                       | - | -   | -    | -1.3 | V    |
|   |   | $I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C            | - | -   | -    | -2.6 | V    |
| t <sub>d</sub>  | delay time  | $I_C = -150 \text{ mA}; I_{Bon} = -15 \text{ mA};$  | - | -   | -    | 12   | ns   |
| t <sub>r</sub>  | rise time   | $I_{Boff}$ = 15 mA; $V_{CC}$ = -10 V;<br>$T_{amb}$ = 25 °C  | - | -   | -    | 30   | ns   |
| t <sub>on</sub>   | turn-on time  | · amb = 0   | - | -   | -    | 40   | ns   |
| t <sub>s</sub>  | storage time  |   | - | -   | -    | 300  | ns   |
| t <sub>f</sub>  | fall time   |   | - | -   | -    | 65   | ns   |
| t <sub>off</sub>  | turn-off time   |   | - | -   | -    | 365  | ns   |
| C <sub>C</sub>  | collector capacitance   | $V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C                              | - | -   | -    | 8    | pF   |
| C <sub>E</sub>  | emitter capacitance   | $V_{EB}$ = -2 V; $I_{C}$ = 0 A; $i_{c}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C                                 | - | -   | -    | 30   | pF   |
| f <sub>T</sub>  | transition frequency  | $V_{CE}$ = -20 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C  | 2 | 200 | -    | -    | MHz  |

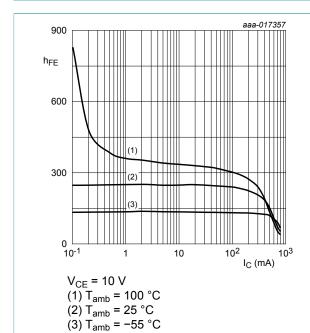


Fig. 2. NPN transistor: DC current gain as a function of collector current; typical values

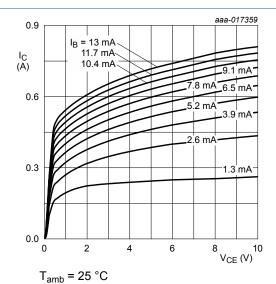


Fig. 3. NPN transistor: Collector current as a function of collector-emitter voltage; typical values

### 40 V, 600 mA NPN/PNP general-purpose transistors

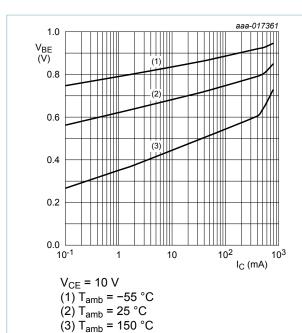


Fig. 4. NPN transistor: Base-emitter voltage as a function of collector current; typical values

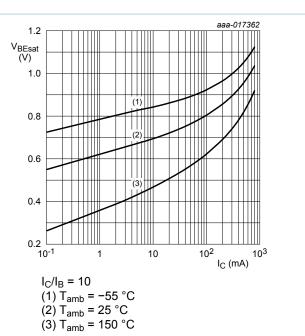


Fig. 5. NPN transistor: Base-emitter saturation voltage as a function of collector current; typical values

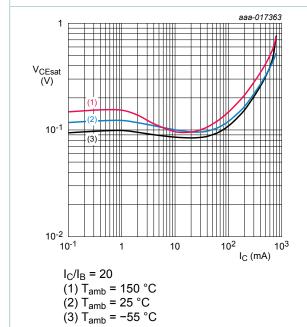
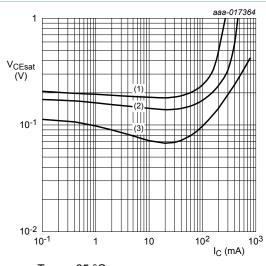


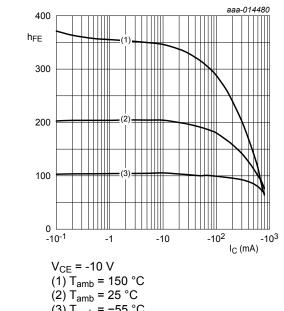
Fig. 6. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \text{ °C}$ (1)  $I_C/I_B = 100$ (2)  $I_C/I_B = 50$ (3)  $I_C/I_B = 10$ 

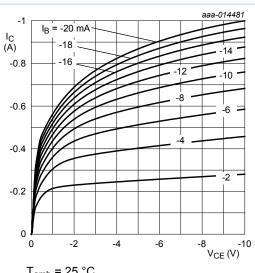
Fig. 7. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values

### 40 V, 600 mA NPN/PNP general-purpose transistors



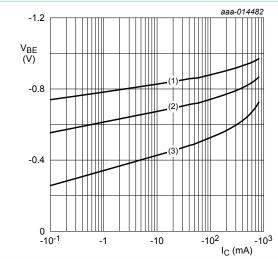
(3)  $T_{amb} = -55 \, ^{\circ}C$ 

PNP transistor: DC current gain as a function Fig. 8. of collector current; typical values



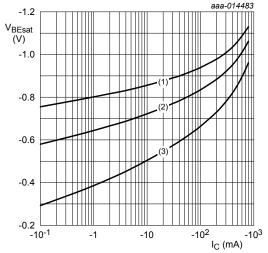
 $T_{amb} = 25 \, ^{\circ}C$ 

PNP transistor: Collector current as a function Fig. 9. of collector-emitter voltage; typical values



$$V_{CE}$$
 = -10 V  
(1)  $T_{amb}$  = -55 °C  
(2)  $T_{amb}$  = 25 °C  
(3)  $T_{amb}$  = 150 °C

Fig. 10. PNP transistor: Base-emitter voltage as a function of collector current; typical values



 $I_C/I_B = 10$ (1)  $T_{amb} = -55$  °C

(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 150 °C

Fig. 11. PNP transistor: Base-emitter saturation voltage as a function of collector current; typical values

## 40 V, 600 mA NPN/PNP general-purpose transistors

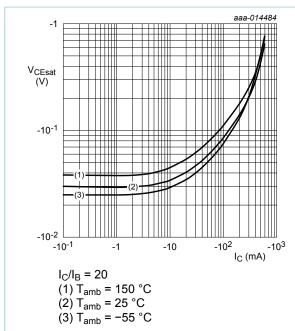


Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

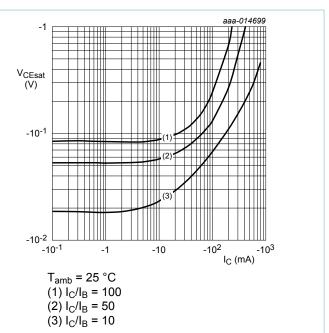


Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

## 40 V, 600 mA NPN/PNP general-purpose transistors

# 11. Test information

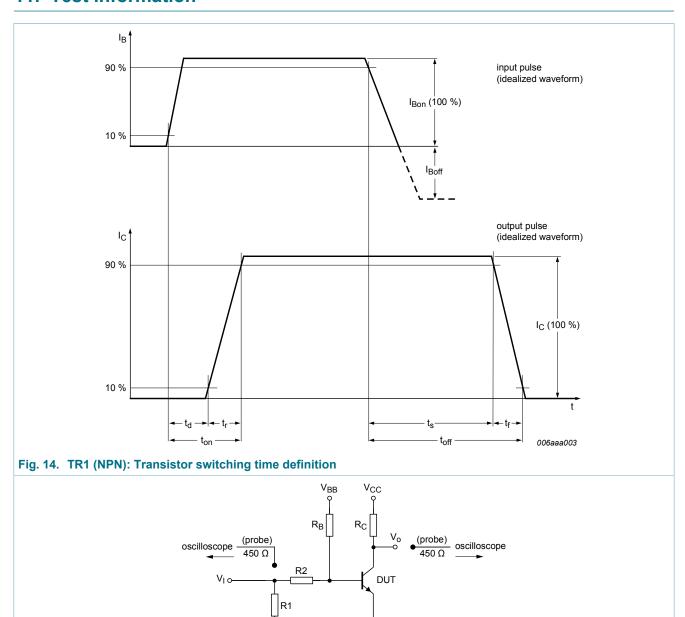
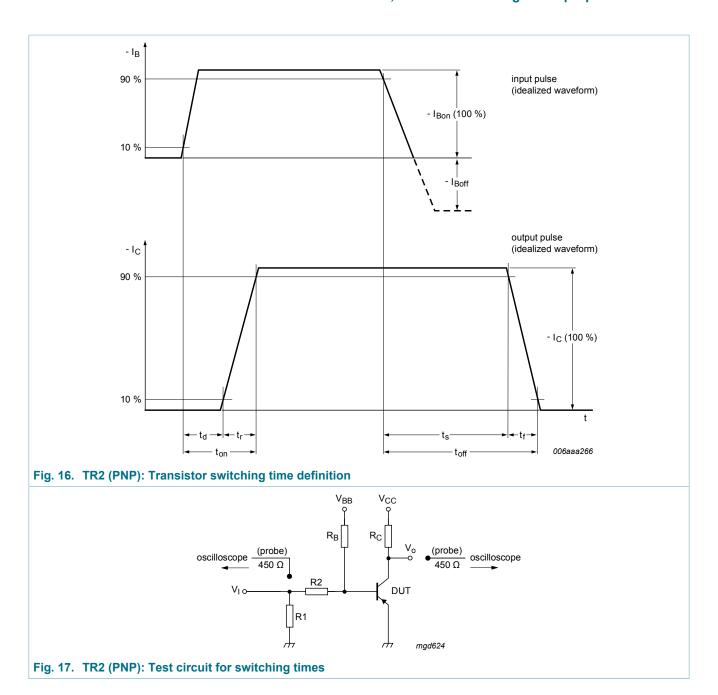


Fig. 15. TR1 (NPN): Test circuit for switching times

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# 40 V, 600 mA NPN/PNP general-purpose transistors

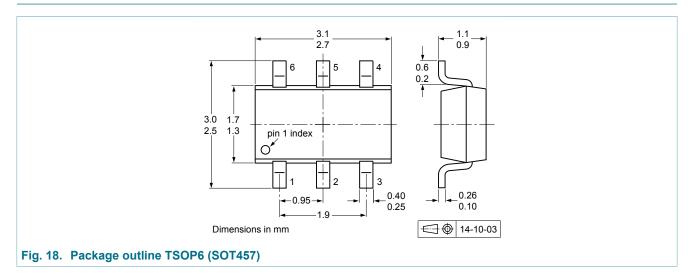


#### **Quality information**

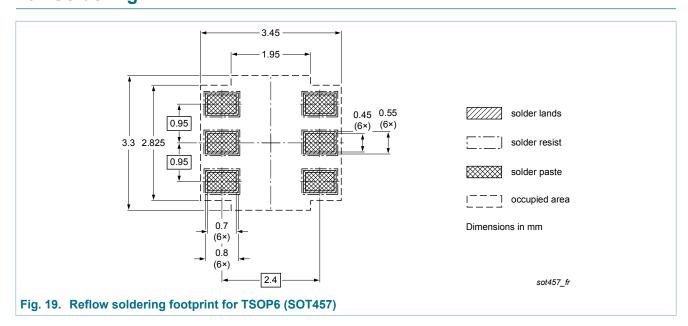
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

40 V, 600 mA NPN/PNP general-purpose transistors

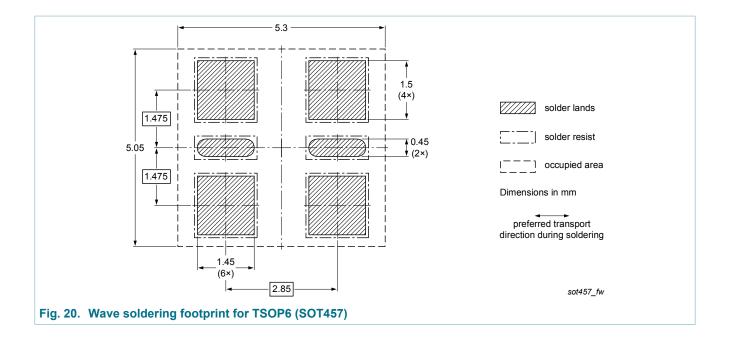
# 12. Package outline



# 13. Soldering



## 40 V, 600 mA NPN/PNP general-purpose transistors



40 V, 600 mA NPN/PNP general-purpose transistors

# 14. Revision history

## **Table 8. Revision history**

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| NMB2227A v.1  | 20160915     | Product data sheet | -             | -          |

#### 40 V, 600 mA NPN/PNP general-purpose transistors

# 15. Legal information

#### **Data sheet status**

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nexperia.com">http://www.nexperia.com</a>.

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40 V, 600 mA NPN/PNP general-purpose transistors

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